In the Specification

Please amend the Title to read:

~~METHOD AND~~ COMPOSITION FOR THE CHEMICAL-VIBRATIONAL-MECHANICAL PLANARIZATION OF COPPER

Please amend paragraph [0024] on page 6 of the specification as follows:

[0024] The CVMPmethod of the present invention employs a chemical mechanical polishing mixture comprising a chemical solution component and a mechanical component, or a plurality of particles, in conjunction with agitation to remove excess material from the underlying substrate. The solution within the mixture comprises at least one etchant, at least one modifier, and lat least one surfactant. The solution to void colume ratio, or the ratio of solution colume to the void volume of the particles within the mixture, is about 1 or less, prefereably about 0.2 or less. The average particle size diameter of the non-abrasive particles within the mixture ranges from about 100 to about 3000 microns (μm), preferably from 500 to ~~1000~~ 2000 μm and more preferably from 1000 to 2000μm. The pH of the mixture may range from 1 to 7, preferably from 1 to 4. The pH of the solution may be adjusted to the desired range using any known acid, base, or amine. However, it is preferable that any acid and/or base used contain substantially no metal ions to avoid introducing undesireable metal components to the solution. Examples of a suitable acid or base[[s]] include ammonium hydroxide and amines, or nitric, phosphoric, sulfuric, or organic acids.